TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U-MOSIII)

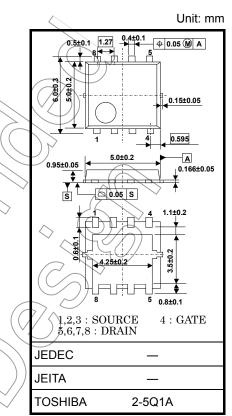
TPCA8014-H

High-Efficiency DC / DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Qsw = 7.4 nC (typ.)
- Low drain-source ON-resistance: $RDS(ON) = 7.1 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 47 \text{ S} (typ.)$
- Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- Enhancement mode: $V_{th} = 1.1$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

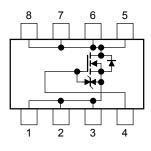
Absolute Maximum Ratings (Ta = 25°C)

			$\langle \cap \rangle$	~	
Characteristic		Symbol	Rating	⊃ _{Unit}	
Drain-source voltage		V _{DSS}	40	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	40	Y	
Gate-source voltage		V _{GSS}	<u>+</u> 20	< <v< td=""></v<>	
Drain current	DC (Note 1)	ID	30	A	
	Pulsed (Note 1)	LDR	90		
Drain power dissipation $(Tc = 25^{\circ}C)$			45	/w	
Drain power dissipation (t = 10 s) (Note 2a)		PD	2.8	W	
Drain power dissipation $(t = 10 s)$ (Note 2b)		PD <		w	
Single-pulse avalanche energy (Note 3)		EAS	84	mJ	
Avalanche current		I _{AR}	30	А	
Repetitive avalanche energy (Tc=25°C) (Note 4)		EAR	2.7	mJ	
Channel temperature		Tch	150	°C	
Storage temperature range		Tstg	–55 to 150	°C	



Weight: 0.068 g (typ.)

Circuit Configuration



Note: For Notes 1 to 5, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

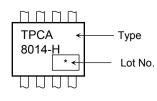
This transistor is an electrostatic-sensitive device. Handle with care.

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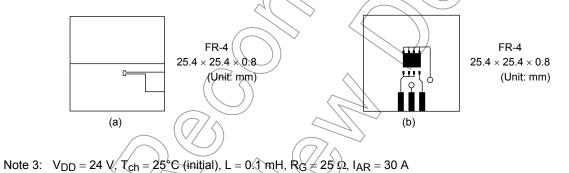
Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W	
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W	

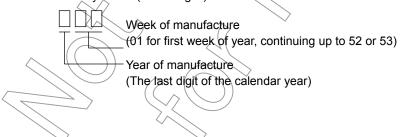
Marking (Note 5)



- Note 1: The channel temperature should not exceed 150°C during use.
- Note 2: (a) Device mounted on a glass-epoxy board (a)
- (b) Device mounted on a glass-epoxy board (b)



- Note 4: Repetitive rating: pulse width limited by max channel temperature
- Note 5: * Weekly code: (Three digits)



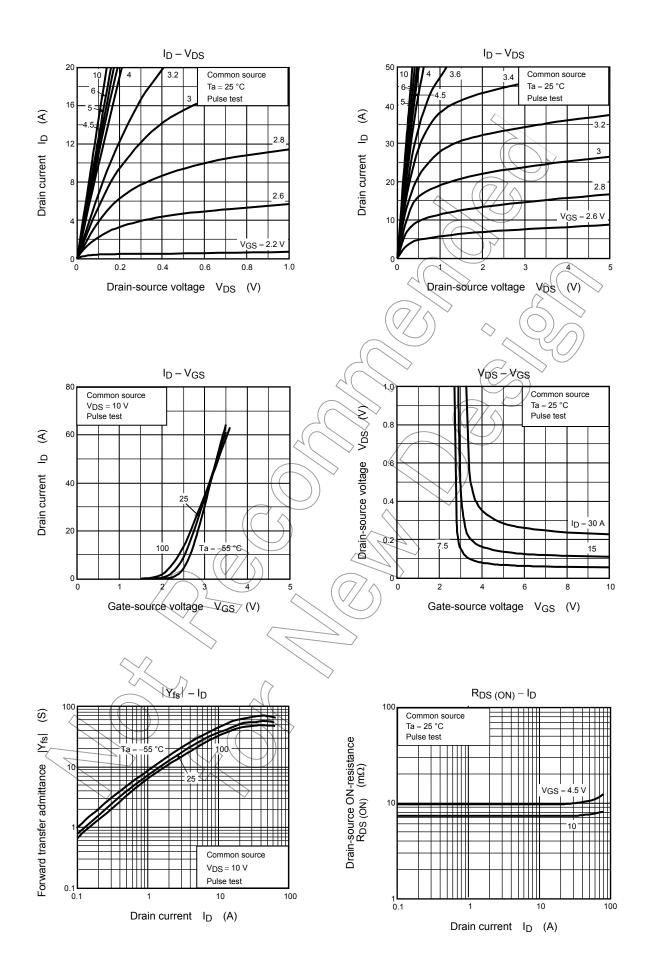
Electrical Characteristics (Ta = 25°C)

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	rrent	I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0~V$	_	—	±10	μA	
Drain cutoff curre	ent	I _{DSS}	$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	—	10	μA	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	40	—	_	V	
		V (BR) DSX	$I_D = 10$ mA, $V_{GS} = -20$ V	25		_	v	
Gate threshold v	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	(11		2.3	V	
Drain-source ON-resistance		R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$		7.1	9.0		
			$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	\mathcal{A}	10.5	14	mΩ	
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	24	47	_	S	
Input capacitance		C _{iss}		_	1365			
Reverse transfer capacitance		C _{rss}		_	110		pF	
Output capacitance		Coss	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} \neq 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		480	\searrow		
Gate resistance		Rg		-6	1.0	> -	Ω	
Switching time	Rise time	tr	10 V N ID = 15 A	K C	45) _		
	Turn-on time	t _{on}			> <u>1</u> 1	_	ns	
	Fall time	t _f			4	_		
	Turn-off time	toff	$V_{DD} \simeq 20 V$ Duty $\leq 1\%$, t _w $\neq 10 \ \mu s$	_	18	_		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 32 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$		22	_		
			$V_{DD} \simeq 32 \text{ V}, \text{ V}_{GS} = 5 \text{ V}, \text{ Ip} = 30 \text{ A}$	_	12	_		
Gate-source cha	rge 1	Qĝs1	\wedge		5.1	_	nC	
Gate-drain ("Miller") charge		Qgd	$V_{DD} \simeq 32 V, V_{GS} = 10 V, I_D = 30 A$	_	4.9	_		
Gate switch char	ge	QSW		_	7.4	_		

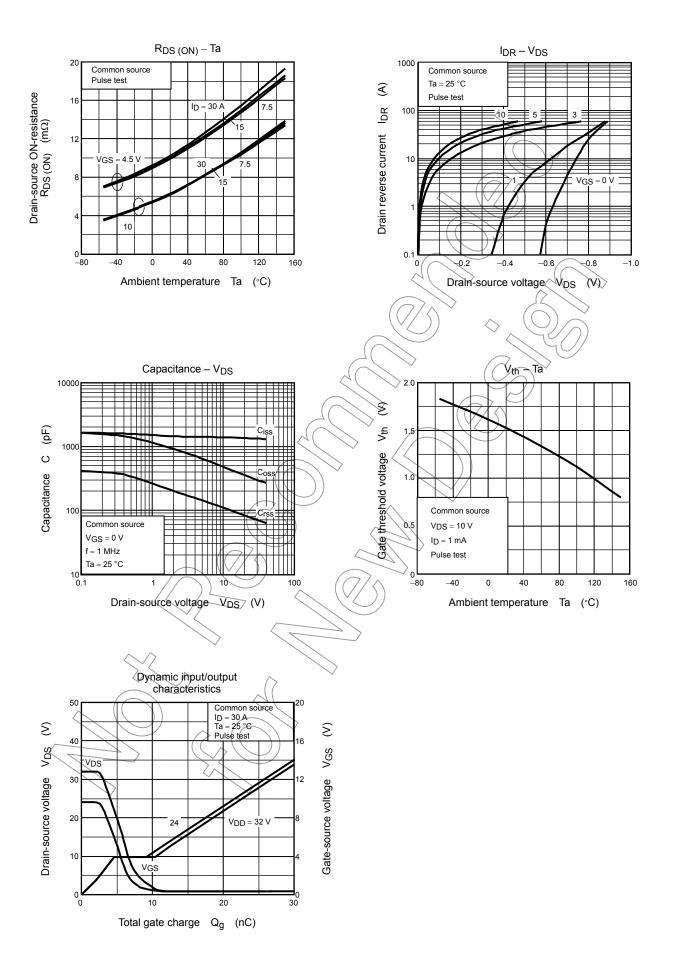
Source-Drain Ratings and Characteristics (Ta \pm 25°C)

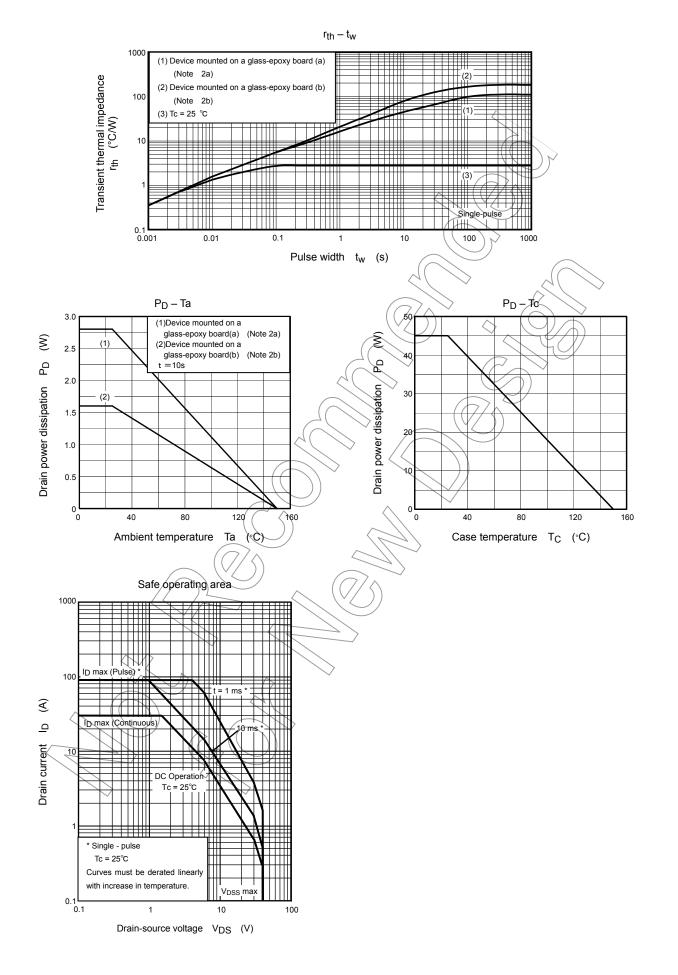
Characteristic	Symbol Test Condition		Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP} —	_	_	90	А
Forward voltage (diode)	V_{DSF} $I_{\text{DR}} = 30 \text{ A}, V_{\text{GS}} = 0 \text{ V}$	_		-1.2	V

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